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48. The thin film transistor of claim 38, wherein said semiconductor film includes oxygen at a concentration of 1x10<sup>19</sup> atoms/cm<sup>3</sup>

## REMARKS

The Advisory Action of October 7, 1997 was received and carefully reviewed. In response thereto, Applicants file a Request Under 37 C.F.R. 1.129 to Withdraw Finality of the Final Rejection for consideration of the *Amendment After Final* filed September 10, 1997. Claims 23, 25, 27 and 32-38 are amended herein and new claims 39-48 are added. Consequently, claims 23-48 are currently pending in the instant application.

Claims 23-28 remain rejected under the judicially created doctrine of obviousness type double patenting over claims 1-21 of U.S. Patent No. 5,313,075 and claims 1-14 of U.S. Patent No. 5,272,654. To overcome this rejection, Applicants filed a Terminal Disclaimer on September 16, 1997.

In addition, claims 23, 25, 27 and 32-38 are amended herein to remove the limitation regarding the concentration of oxygen, carbon or nitrogen in the semiconductor layer or film. This feature is now recited in dependent claims 39-48 which depend from amended claims 23, 25, 27 and 32-38, respectively. For the reasons advanced by Applicants in the September 10 *Amendment After Final*, consideration and allowance of these claims is now respectfully requested.

In view of the foregoing, it is respectfully requested that the rejections of record be reconsidered and withdrawn by the Examiner, that claims 23-38 be allowed, that new claims 39-48 be allowed and that the application be passed to issue. If the Examiner believes a conference would be of benefit in expediting the prosecution of the instant application, she is hereby invited to telephone counsel to arrange such a conference.

Respectfully submitted,

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